2N3663





# **NPN RF Transistor**

This device is designed for use as RF amplifiers, oscillators and multipliers with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 43. See PN918 for characteristics.

### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	12	V
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	3.0	V
I <sub>C</sub>	Collector Current - Continuous	50	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES: 1) These ratings are based on a maximum junction temperature of 150 degrees C. 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах	Units
		2N3663	
P <sub>D</sub>	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta_{JC}}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

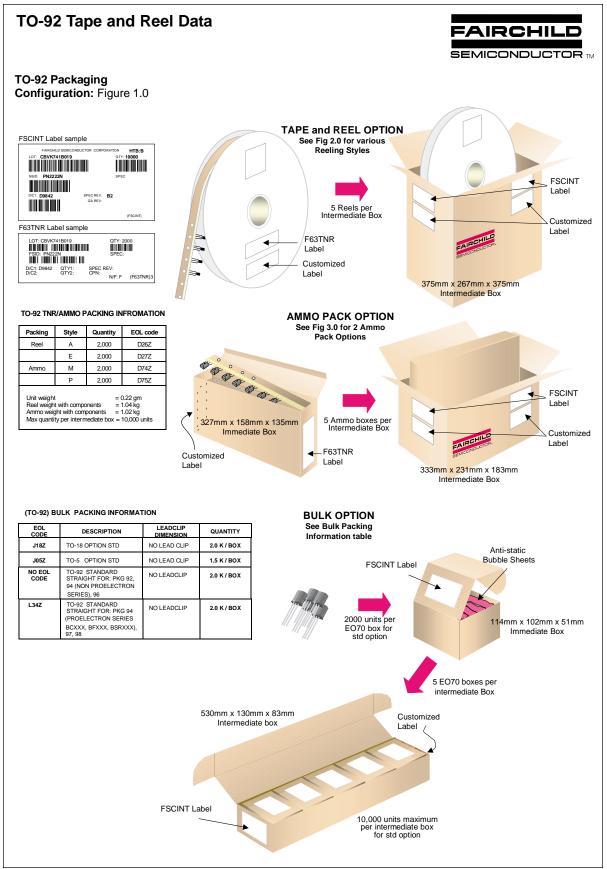
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# NPN RF Transistor

(continued)

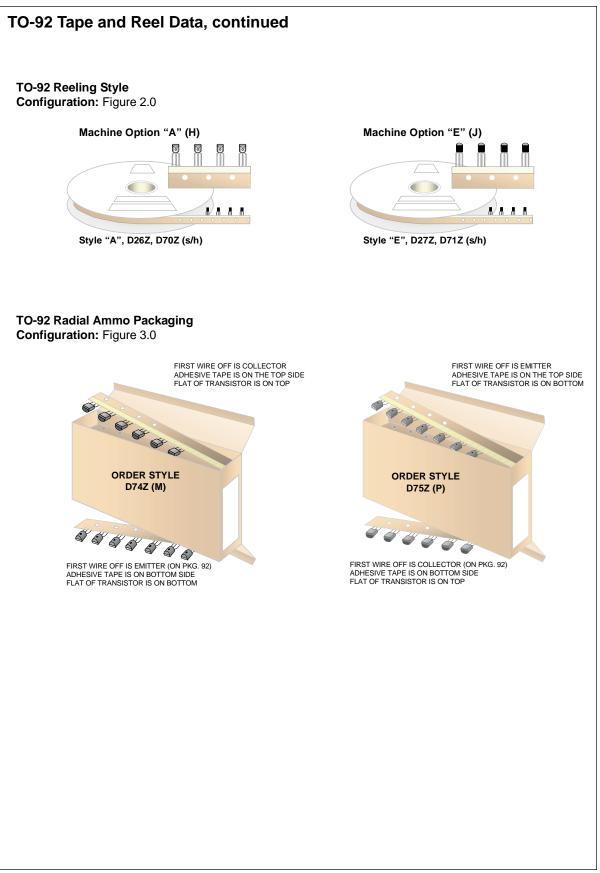
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
√ <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	12		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	30		V
/ <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 100 \ \mu {\rm A}, \ I_{\rm C} = 0$	3.0		V
СВО	Collector-Cutoff Current	$V_{CB} = 15 \text{ V}, \text{ I}_{E} = 0$		0.5	μA
EBO	Emitter-Cutoff Current	$V_{EB} = 2.0 \text{ V}, I_{C} = 0$		0.5	μA
η <sub>FE</sub>	DC Current Gain	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 8.0 \text{ mA}$	20		
ON CHAF	RACTERISTICS*				
IFE	DC Current Gain	$v_{CE} = 10 v, i_C = 8.0 \text{ IIIA}$	20		
SMALL SI	GNAL CHARACTERISTICS				
	GNAL CHARACTERISTICS Current Gain - Bandwidth Product	$I_{c} = 5.0 \text{ mA}, V_{ce} = 10 \text{ V},$ f = 100 MHz	700	2100	MHz
fT		0 / 02 /	700	2100	MHz pF
f <sub>T</sub> C <sub>ob</sub>	Current Gain - Bandwidth Product	f = 100 MHz			
f <sub>T</sub> C <sub>ob</sub>	Current Gain - Bandwidth Product Output Capacitance			1.7	pF
T C <sub>ob</sub> b'C <sub>C</sub>	Current Gain - Bandwidth Product Output Capacitance			1.7	pF
ft C <sub>ob</sub> rb'C <sub>C</sub> FUNCTIO	Current Gain - Bandwidth Product Output Capacitance Collector Base Time Constant			1.7	pF
T C <sub>OD</sub> TO'C <sub>C</sub> FUNCTIO NF	Current Gain - Bandwidth Product Output Capacitance Collector Base Time Constant NAL TEST Noise Figure	$\begin{array}{l} f = 100 \text{ MHz} \\ V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz} \\ I_C = 8.0 \text{ mA}, V_{CE} = 10 \text{ V}, \\ f = 79.8 \text{ MHz} \\ \end{array}$ $\begin{array}{l} I_C = 1.0 \text{ mA}, V_{CE} = 6.0 \text{ V}, \\ f = 60 \text{ MHz}, \text{ Rg} = 400 \Omega \end{array}$	0.8	1.7 80	pF pS dB
f <sub>T</sub> C <sub>ob</sub> rb'C <sub>C</sub> FUNCTIO	Current Gain - Bandwidth Product Output Capacitance Collector Base Time Constant			1.7 80	pF pS
f <sub>T</sub> C <sub>ob</sub> rb'C <sub>C</sub> FUNCTIO NF G <sub>pe</sub>	Current Gain - Bandwidth Product Output Capacitance Collector Base Time Constant NAL TEST Noise Figure Amplifier Power Gain		0.8	1.7 80	pF pS dB
f <sub>T</sub> C <sub>ob</sub> rb'C <sub>C</sub> FUNCTIO NF G <sub>pe</sub>	Current Gain - Bandwidth Product Output Capacitance Collector Base Time Constant NAL TEST Noise Figure		0.8	1.7 80	pF pS dB
f <sub>T</sub> C <sub>ob</sub> rb'C <sub>C</sub> FUNCTIO NF G <sub>pe</sub>	Current Gain - Bandwidth Product Output Capacitance Collector Base Time Constant NAL TEST Noise Figure Amplifier Power Gain		0.8	1.7 80	pF pS dB

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